

# Hex Inverter (Unbuffered) MC74LVXU04

The MC74LVX04 is an advanced high speed CMOS unbuffered hex inverter. The inputs tolerate voltages up to  $6.5~\rm{V}$ , allowing the interface of  $5.0~\rm{V}$  systems to  $3.0~\rm{V}$  systems.

#### **Features**

- High Speed:  $t_{PD} = 4.1 \text{ ns (Typ)}$  at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: V<sub>OLP</sub> = 0.5 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- These Devices are Pb-Free and are RoHS Compliant

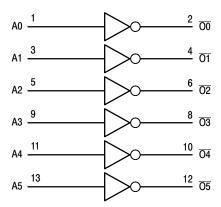


Figure 1. Logic Diagram

#### **PIN NAMES**

Pins	Function
An	Data Inputs
On	Outputs

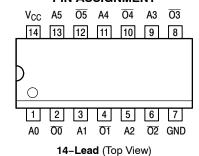
## **FUNCTION TABLE**

An	<del>On</del>
L	H
Н	L

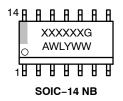


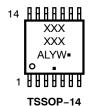


PIN ASSIGNMENT



## **MARKING DIAGRAMS**





XXXXXX = Specific Device Code A = Assembly Location

A = Assembly Location
WL, L = Wafer Lot
Y = Year

WW, W = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

# MC74LVXU04

#### **MAXIMUM RATINGS**

Symbol	Para	nmeter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +6.5	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +6.5	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>I</sub> < GND	-20	mA
I <sub>OK</sub>	DC Output Diode Current	V <sub>O</sub> < GND	±20	mA
lout	DC Output Sink Current		±25	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±50	mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C	
TL	Lead Temperature, 1 mm from Case for 10 S	260	°C	
TJ	Junction Temperature under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance	SOIC TSSOP	116 150	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 25°C	SOIC TSSOP	1077 833	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% - 35%	UL 94-V0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Charged Device Model (Note 2)	> 2000 2000	V
I <sub>Latchup</sub>	Latchup Performance Ab	pove V <sub>CC</sub> and Below GND at 85°C (Note 3)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to JESD22-C101-A.
- 3. Tested to EIA/JESD78.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Supply Voltage	2.0	3.6	V
VI	Input Voltage (Note 4)	0	5.5	V
V <sub>O</sub>	Output Voltage (HIGH or LOW State)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Free–Air Temperature	-40	+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate $V_{CC}$ = 3.0 V $\pm$ 0.3 V	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

4. Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

#### MC74LVXU04

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>		T <sub>A</sub> = 25°C		$T_A = -40$	to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		٧
V <sub>IL</sub>	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	<b>V</b>
V <sub>OH</sub>	High-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		٧
V <sub>OL</sub>	Low-Level Output Voltage (V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub> )	$I_{OL} = 50 \mu A$ $I_{OL} = 50 \mu A$ $I_{OL} = 4 \text{ mA}$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	٧
I <sub>in</sub>	Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	3.6			±0.1		±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	3.6			2.0		20.0	μΑ

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$ )

				T <sub>A</sub> = 25°C		T <sub>A</sub> = -40 to 85°C			
Symbol	Parameter	Test Cond	itions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay, Input to Output	V <sub>CC</sub> = 2.7V	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.4 7.9	10.1 13.6	1.0 1.0	12.5 16.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15 pF$ $C_L = 50 pF$		4.1 6.6	6.2 9.7	1.0 1.0	7.5 11.0	
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 5)	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$	C <sub>L</sub> = 50 pF C <sub>L</sub> = 50 pF			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

## **CAPACITIVE CHARACTERISTICS**

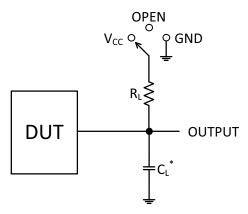
		T <sub>A</sub> = 25°C		T <sub>A</sub> = -40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)		18				pF

<sup>6.</sup>  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/6$  (per buffer).  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

# **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.5	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.5	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

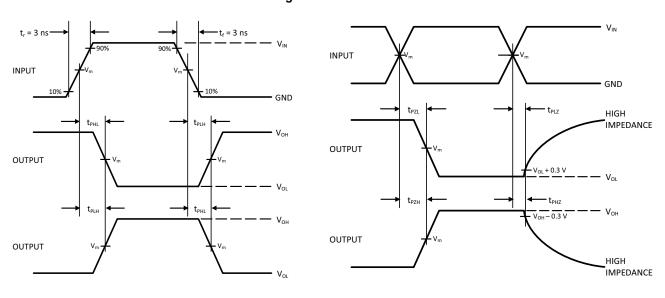
# MC74LVXU04



Test	Switch Position	C <sub>L</sub>	$R_{L}$
t <sub>PLH</sub> / t <sub>PHL</sub>	Open	See AC Characteristics	1 kΩ
t <sub>PLZ</sub> / t <sub>PZL</sub>	V <sub>CC</sub>	Table	
t <sub>PHZ</sub> / t <sub>PZH</sub>	GND		

\*C<sub>L</sub> Includes probe and jig capacitance

Figure 2. Test Circuit



Device	V <sub>IN</sub> , V	V <sub>m</sub> , V
MC74LVXU04	V <sub>CC</sub>	50% x V <sub>CC</sub>

Figure 3. Switching Waveforms

# **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
MC74LVXU04DR2G	LVXU04	SOIC-14 NB (Pb-Free)	2500 Tape & Reel
MC74LVXU04DTR2G	LVX U04	TSSOP-14 (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

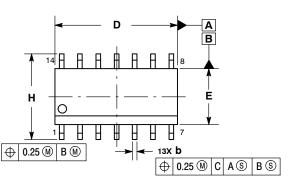


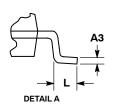


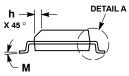
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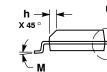
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 





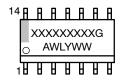




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.35	1.75	0.054	0.068	
A1	0.10	0.25	0.004	0.010	
АЗ	0.19	0.25	0.008	0.010	
b	0.35	0.49	0.014	0.019	
D	8.55	8.75	0.337	0.344	
Е	3.80	4.00	0.150	0.157	
œ	1.27	BSC	0.050	BSC	
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.019	
L	0.40	1.25	0.016	0.049	
М	0 °	7°	0 °	7°	

# **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

# **SOLDERING FOOTPRINT\***

1	6.50	14X 1.18
		] 1
<del>-</del>		1.27 PITCH
14X 0.58		] <del></del>
		]

**DIMENSIONS: MILLIMETERS** 

# **STYLES ON PAGE 2**

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# SOIC-14 CASE 751A-03 ISSUE L

# DATE 03 FEB 2016

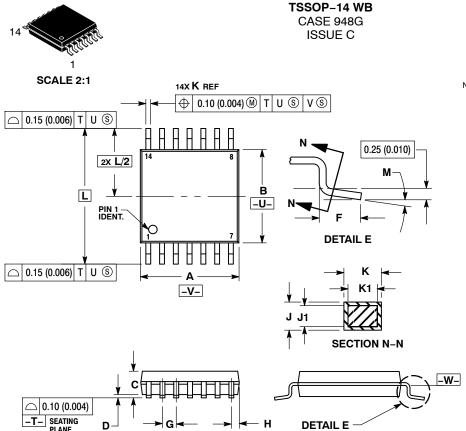
STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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**DATE 17 FEB 2016** 





- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  TERMINAL NUMBERS ARE SHOWN FOR DEEEDENIC OMITY.
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
м	o °	8 °	o °	a °

## **GENERIC MARKING DIAGRAM\***



= Assembly Location

L = Wafer Lot = Year = Work Week W

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

# **RECOMMENDED SOLDERING FOOTPRINT\***

-	7.06
1	
<del></del>	
	0.65 PITCH
<b>↓</b> □	
14X 0.36 126	<del></del>
0.36 - 1.26	DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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